

ABSTRACT OF THE DISCLOSURE

The semiconductor photodetecting device comprises a PIN photodiode formed on an SI-InP substrate 10; a buried optical waveguide portion 12a formed on the SI-InP substrate 10 and including the film thickness continuously increased toward the PIN photodiode 32 and an InP clad layer 20a covering the upper surface and the side surface of the InGaAsP core layer 18; and a ridge-shaped connection optical waveguide portion 12b formed on the SI-InP substrate 10 between the PIN photodiode 32 and the buried optical waveguide portion 12a and including the InGaAsP core layer 18 and the InP clad layer 20a selectively covering only the upper surface of the InGaAsP core layer 18.